

**CMHSH-3**  
**SURFACE MOUNT**  
**SCHOTTKY DIODE**



# Central<sup>TM</sup>

## Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMHSH-3 type is a Silicon Schottky diode, epoxy molded in a SOD-123 surface mount package, designed for fast switching applications requiring a low forward voltage drop.

**Marking Code is CH3.**

MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

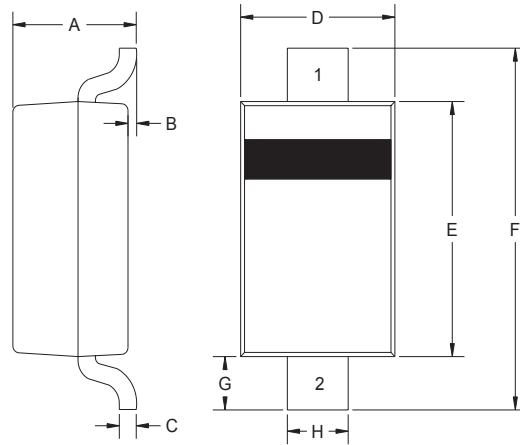
	<u>SYMBOL</u>		<u>UNITS</u>
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	30	V
Continuous Forward Current	I <sub>F</sub>	200	mA
Peak Repetitive Forward Current	I <sub>FRM</sub>	300	mA
Forward Surge Current, tp<1.0s	I <sub>FSM</sub>	600	mA
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	-65 to +125	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	650	°C/W

ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I <sub>R</sub>	V <sub>R</sub> =25V			2.0	μA
V <sub>BR</sub>	I <sub>R</sub> =100μA	30			V
V <sub>F</sub>	I <sub>F</sub> =100μA			240	mV
V <sub>F</sub>	I <sub>F</sub> =1.0mA			320	mV
V <sub>F</sub>	I <sub>F</sub> =10mA			400	mV
V <sub>F</sub>	I <sub>F</sub> =30mA			500	mV
V <sub>F</sub>	I <sub>F</sub> =100mA			1000	mV
C <sub>T</sub>	V <sub>R</sub> =1.0V, f=1 MHz		10		pF
t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, R <sub>L</sub> =100Ω, Rec. to 1.0mA		10		ns



**MECHANICAL OUTLINE - SOD-123**



R3

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	-	0.005	-	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.112	2.50	2.84
F	0.140	0.154	3.55	3.90
G	0.010	-	0.25	-
H	0.020	0.028	0.50	0.70

SOD-123 (REV:R3)

**Lead Code:**

- 1) Cathode**
- 2) Anode**

**Marking Code is CH3.**

R2 ( 2-November 2001)